

7.5 at% of N with respect to the amount of the first element, of at least one second element selected from the group consisting of C, O, N and H, provided that an amount of N is not more than 3000 at ppm, and the balance of Al.

8. (New) The sputter target according to claim 7, wherein the sputter target comprises an intermetallic compound of Al and the first element, and the intermetallic compound is precipitated finely and uniformly in the sputter target.

9. (New) The sputter target according to claim 8, wherein the sputter target is formed by applying a quench coagulation method.

10. (New) The sputter target according to claim 7, wherein the sputter target contains the C in the range of 3000 at ppm or below with respect to the amount of the first element.

11. (New) The sputter target according to claim 7, wherein the sputter target contains the C in the range of 1500 at ppm or below with respect to the amount of the first element.

12. (New) The sputter target according to claim 7, wherein the sputter target contains the O in the range of 1.5 at% or below with respect to the amount of the first element.

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13. (New) The sputter target according to claim 7, wherein the sputter target contains the O in the range of 1500 at ppm or below with respect to the amount of the first element.
14. (New) The sputter target according to claim 7, wherein the sputter target contains the N in the range of 1.5 at% or below with respect to the amount of the first element.
15. (New) The sputter target according to claim 14, wherein the sputter target is formed by applying a quench coagulation method.
16. (New) The sputter target according to claim 7, wherein the sputter target contains the N in the range of 3000 at ppm or below with respect to the amount of the first element.
17. (New) The sputter target according to claim 16, wherein the sputter target is formed by applying a quench coagulation method.
18. (New) The sputter target of claim 7, wherein the sputter target contains the N in the range of 1500 at pm or below with respect to the amount of the first element.
19. (New) The sputter target according to claim 18, wherein the sputter target is formed by applying a quench coagulation method.

20. (New) The sputter target according to claim 7, wherein the sputter target contains the H in the range of 1.5 at % or below with respect to the amount of the first element.
21. (New) The sputter target according to claim 7, wherein the sputter target contains the H in the range of 1500 at ppm or below with respect to the amount of the first element.
22. (New) The sputter target according to claim 7, wherein the sputter target is used for forming an interconnector line of thin film of a liquid crystal display.
23. (New) A sputter target, consisting essentially of 0.001 to 30 at% of at least one first element selected from the group consisting of Ag, Au, Cu, Ti, V, Nb, Ta, Cr, Mo, W, Mn, Fe, Co, Ni, Pd, Ir, Pt, Cd, Si and Pb, at least one second element selected from the group consisting of 0.01 at ppm to 3 at% of C with respect to the amount of the first element, 0.01 at ppm to 7.5 at% of O with respect to the amount of the first element, 0.01 at ppm to 7.5 at% of N with respect to the amount of the first element, and 0.01 at ppm to 7.5 at% of H with respect to the amount of the first element, the second element comprising the H, and the balance of Al.

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24. (New) The sputter target according to claim 23, wherein the sputter target contains the H in the range of 1.5 at% or below with respect to the amount of the first element.
25. (New) The sputter target according to claim 23, wherein the sputter target contains the H in the range of 1500 at ppm or below with respect to the amount of the first element.
26. (New) The sputter target according to claim 23, wherein the sputter target contains the H in the range of 500 wt ppm or below.
27. (New) The sputter target according to claim 23, wherein the sputter target contains the C in the range of 3000 at ppm or below with respect to the amount of the first element.
28. (New) The sputter target according to claim 23, wherein the sputter target contains the C in the range of 1500 at ppm or below with respect to the amount of the first element.
29. (New) The sputter target according to claim 23, wherein the sputter target contains the O in the range of 1.5 at% or below with respect to the amount of the first element.

30. (New) The sputter target according to claim 23, wherein the sputter target contains the O in the range of 1500 at ppm or below with respect to the amount of the first element.
31. (New) The sputter target according to claim 23, wherein the sputter target contains the N in the range of 1.5 at% or below with respect to the amount of the first element.
32. (New) The sputter target according to claim 23, wherein the sputter target contains the N in the range of 1500 at ppm or below with respect to the amount of the first element.